

INCHANGE SEMICONDUCTOR

isc Silicon PNP Power Transistor

2SA1012-D

DESCRIPTION

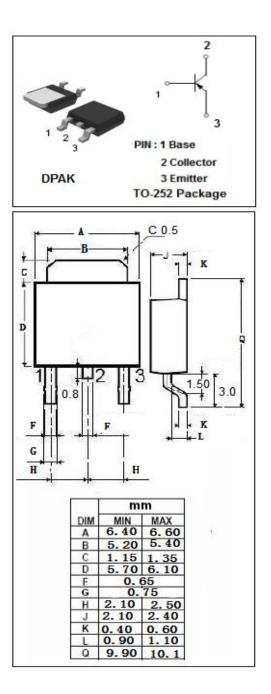
- Low Collector Saturation Voltage
 :V_{CE(sat)}= -0.4(V)(Max)@I_C= -3A
- High Switching Speed
- "-D" = TO-252 Package
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

• Designed for high current switching applications.

| SYMBO L | PARAMETER | VALUE | UNIT | | | | |
|------------------|--|---------|------|--|--|--|--|
| V _{CBO} | Collector-Base Voltage | -60 | V | | | | |
| V _{CEO} | Collector-Emitter Voltage | -50 | V | | | | |
| V _{EBO} | Emitter-Base Voltage | -5 | V | | | | |
| lc | Collector Current-Continuous | -5 | A | | | | |
| Pc | Total Power Dissipation @ T _C =25℃ | 20 | W | | | | |
| TJ | Junction Temperature | 150 | Ĉ | | | | |
| T _{stg} | Storage Temperature Range | -55~150 | Ĉ | | | | |

ABSOLUTE MAXIMUM RATINGS(T₂=25℃)



ELECTRICAL CHARACTERISTICS

$\mathsf{Tc}\text{=}25\,^\circ\!\!\mathbb{C}$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | МАХ | UNIT |
|----------------------|--------------------------------------|---|-----|------|------|------|
| $V_{(BR)CEO}$ | Collector-Emitter Breakdown Voltage | I _C = -10mA ; I _B = 0 | -50 | | | V |
| V _{CE(sat)} | Collector-Emitter Saturation Voltage | I _C = -3Α; I _B = -0.15Α | | | -0.4 | V |

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| V _{BE(sat)} | Base-Emitter Saturation Voltage | I _C = -3A; I _B = -0.15A | | | -1.2 | V |
|----------------------|---------------------------------|--|----|-----|------|-----|
| Ісво | Collector Cutoff Current | V _{CB} = -50V ; I _E = 0 | | | -1 | μ Α |
| I _{EBO} | Emitter Cutoff Current | V _{EB} = -5V; I _C = 0 | | | -1 | μ Α |
| h _{FE-1} | DC Current Gain | I _C = -1A ; V _{CE} = -1V | 70 | | 240 | |
| h _{FE-2} | DC Current Gain | Ic= -3A ; Vce= -1V | 30 | | | |
| f⊤ | Current-Gain—Bandwidth Product | I _C = -1A ; V _{CE} = -4V | | 60 | | MHz |
| Сов | Output Capacitance | I _E = 0; V _{CB} = -10V; f _{test} = 1MHz | | 170 | | pF |

Switching Times

| ton | Turn-on Time | | 0.1 | μ S |
|------------------|--------------|---|-----|------------|
| t _{stg} | Storage Time | I _C = -3A ,R _L = 10 Ω , I _{B1} = -I _{B2} = -0.15A,V _{CC} = -30V | 1.0 | μ S |
| t _f | Fall Time | | 0.1 | μ \$ |

h_{FE-1} Classifications

| 0 | Y | |
|--------|---------|--|
| 70-140 | 120-240 | |

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